

### REMARKS

As required by the Examiner, the title has been amended, and FIGS. 15-18 have been labeled with the legend "Prior Art."

Claim 7 has been canceled. Therefore, the rejections of that claim are moot.

The remaining claims were rejected as anticipated by U.S. Patent No. 5,328,859 (Vo et al.).

Independent claims 1 and 8 relate to a semiconductor device that includes a gate electrode, a source, and a drain that includes three regions (drain region, drift region and impurities region).

As shown in the example of FIG. 7, the drain (on the right-hand side of the figure) includes a high-concentration region 12 surrounded by a low-concentration drift region 4 with an additional impurity region 7A. The impurity region 7A has a concentration that is greater than the concentration of the drift region 4, but lower than the concentration of the drain 12.

Claims 1 and 8 have been amended to recite that the drift region (which is more lightly doped than the impurities region) extends deeper into the semiconductor layer than the impurities region. For example, as shown in FIG. 7, the drift region 4 is more lightly doped than the impurities region 7A and extends deeper into the semiconductor layer 2.

The Vo et al. Patent discloses a PMOS transistor 6 (left-hand side of FIG. 2j) that includes a gate 28, a source contact 14 and a drain contact 20. In addition to the contact 20, the drain region (D) includes low concentration drift regions 16 and a higher concentration drift region 18. The concentration of the drain contact 20 is higher than the concentration of the drift region 18 (col. 3, lines 10). Thus, the carrier concentration in the drift region  $d_1$  is lower than the concentration in the region  $d_2$ , which, in turn, is lower than the concentration in the contact region  $d_3$  (col. 3, lines 14-19).

In contrast to the subject matter of the pending claims, the lower concentration region (defined by drift region 16) does not extend deeper into the n-well than the mid-level concentration region (defined by drift region 18). Instead, the drift region 18 extends deeper than the drift region 16. That is precisely the opposite of what is recited in the claims, as amended.

In view of the foregoing remarks, applicant respectfully requests withdrawal of the rejections of claims 1 and 8. The dependent claims should be allowed at least for the same reasons.

It is believed that all of the pending claims have been addressed. However, the absence of a reply to a specific rejection, issue or comment does not signify agreement with or concession of that rejection, issue or comment. In addition, because the arguments made above may not be exhaustive, there may be reasons for patentability of any or all pending claims (or other claims) that have not been expressed. Finally, nothing in this paper should be construed as an intent to concede any issue with regard to any claim, except as specifically stated in this paper, and the amendment of any claim does not necessarily signify concession of unpatentability of the claim prior to its amendment.

Applicant : Shuichi Kikuchi et al.  
Serial No. : 10/651,855  
Filed : August 29, 2003  
Page : 9 of 9

Attorney's Docket No.: 10417-057002 / F51-  
160880M/SW

Please apply any charges or credits to deposit account 06-1050.

Respectfully submitted,

Date: 2/24/2005



Samuel Borodach  
Reg. No. 38,388

Fish & Richardson P.C.  
Citigroup Center  
52nd Floor  
153 East 53rd Street  
New York, New York 10022-4611  
Telephone: (212) 765-5070  
Facsimile: (212) 258-2291

30211274.doc

Applicant : Shuichi Kikuchi et al.  
Serial No. : 10/651,855  
Filed : August 29, 2003  
Page : 6 of 9

Attorney's Docket No.: 10417-057002 / F51-  
160880M/SW

Amendments to the Drawings:

The attached replacement sheets of drawings include changes to FIGS. 15-18 and replace the original sheet including those figures.

As required by the Examiner, FIGS. 15-18 have been labeled with the legend "Prior Art."

Attachments following last page of this Amendment:

Replacement Sheets (2 pages)